



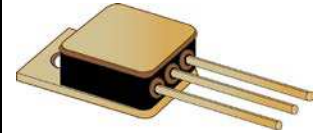
N-CHANNEL MOSFET
Qualified per MIL-PRF-19500/543

Qualified Levels:
JAN, JANTX, and
JANTXV

DESCRIPTION

This family of 2N6764T1, 2N6766T1, 2N6768T1 and 2N6770T1 switching transistors are military qualified up to the JANTXV level for high-reliability applications. These devices are also available in a thru hole TO-204AE metal can package. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.



TO-254AA Package

FEATURES

- JEDEC registered 2N6764, 2N6766, 2N6768 and 2N6770 number series.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/543. (See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

Also available in:

**TO-204AE (TO-3)
package**



(lead)
[2N6764 & 2N6770](#)

APPLICATIONS / BENEFITS

- Low-profile design.
- Military and other high-reliability applications.

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise stated

Parameters / Test Conditions	Symbol	Value	Unit
Junction & Storage Temperature Range	T _J & T _{stg}	-55 to +150	°C
Thermal Resistance Junction-to-Case	R _{θJC}	0.83	°C/W
Total Power Dissipation	P _T	4 150	W
		@ T _A = +25 °C @ T _C = +25 °C ⁽¹⁾	
Drain-Source Voltage, dc	V _{DS}	100 200 400 500	V
		2N6764T1 2N6766T1 2N6768T1 2N6770T1	
Gate-Source Voltage, dc	V _{GS}	± 20	V
Drain Current, dc @ T _C = +25 °C ⁽²⁾	I _{D1}	38.0 30.0 14.0 12.0	A
		2N6764T1 2N6766T1 2N6768T1 2N6770T1	
Drain Current, dc @ T _C = +100 °C ⁽²⁾	I _{D2}	24.0 19.0 9.0 7.75	A
		2N6764T1 2N6766T1 2N6768T1 2N6770T1	
Off-State Current (Peak Total Value) ⁽³⁾	I _{DM}	152 120 56 48	A (pk)
		2N6764T1 2N6766T1 2N6768T1 2N6770T1	
Source Current	I _S	38.0 30.0 14.0 12.0	A
		2N6764T1 2N6766T1 2N6768T1 2N6770T1	

Notes featured on next page.

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- NOTES:**
- Derate linearly by 1.2 W/°C for $T_c > +25$ °C.
 - The following formula derives the maximum theoretical I_D limit. I_D is limited by package and internal wires and may also be limited by pin diameter:

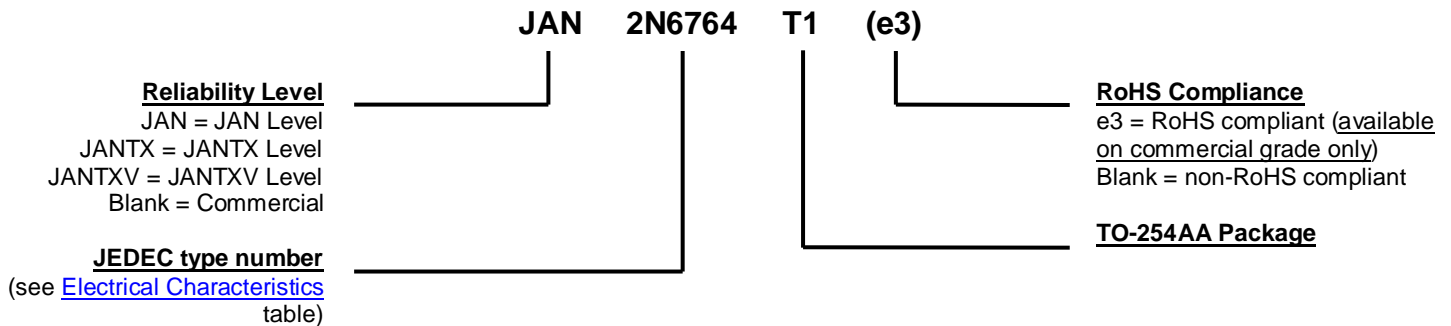
$$I_D = \sqrt{\frac{T_J(\max) - T_c}{R_{\theta JC} \times R_{DS(on)} @ T_J(\max)}}$$

- $I_{DM} = 4 \times I_{D1}$ as calculated in note 2.

MECHANICAL and PACKAGING

- CASE: Nickel plated, hermetically sealed, TO-254AA.
- TERMINALS: Ni plated, copper cored, kovar.
- MARKING: Manufacturers ID, part number, date code, Beo (Beryllium Oxide).
- WEIGHT: 6.5 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
di/dt	Rate of change of diode current while in reverse-recovery mode, recorded as maximum value.
I_F	Forward current
R_G	Gate drive impedance
V_{DD}	Drain supply voltage
V_{DS}	Drain source voltage, dc
V_{GS}	Gate source voltage, dc

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$, unless otherwise noted

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 $V_{(BR)DSS}$	100 200 400 500		V
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = +125\text{ }^\circ\text{C}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = -55\text{ }^\circ\text{C}$	$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	V
Gate Current $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}, T_J = +125\text{ }^\circ\text{C}$	I_{GSS1} I_{GSS2}		± 100 ± 200	nA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 I_{DSS1}		25	μA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 200\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 500\text{ V}, T_J = +125\text{ }^\circ\text{C}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 I_{DSS2}		1.0	mA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}, T_J = +125\text{ }^\circ\text{C}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 I_{DSS3}		0.25	mA
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 24.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 19.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 9.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 7.75\text{ A pulsed}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 $r_{DS(on)1}$		0.055 0.085 0.3 0.4	Ω
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 38.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 30.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 14.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 12.0\text{ A pulsed}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 $r_{DS(on)2}$		0.065 0.09 0.4 0.5	Ω
Static Drain-Source On-State Resistance $T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 10\text{ V}, I_D = 24.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 19.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 9.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 7.75\text{ A pulsed}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 $r_{DS(on)3}$		0.094 0.153 0.66 0.88	Ω
Diode Forward Voltage $V_{GS} = 0\text{ V}, I_D = 38.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 30.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 14.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 12.0\text{ A pulsed}$	2N6764T1 2N6766T1 2N6768T1 2N6770T1 V_{SD}		1.9 1.9 1.7 1.7	V

ELECTRICAL CHARACTERISTICS @ T_A = +25 °C, unless otherwise noted (continued)
DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate Charge:				
On-State Gate Charge	Q _{g(on)}			nC
V _{GS} = 10 V, I _D = 38.0 A, V _{DS} = 50 V 2N6764T1			125	
V _{GS} = 10 V, I _D = 30.0 A, V _{DS} = 100 V 2N6766T1			115	
V _{GS} = 10 V, I _D = 14.0 A, V _{DS} = 200 V 2N6768T1			110	
V _{GS} = 10 V, I _D = 12.0 A, V _{DS} = 250 V 2N6770T1			120	
Gate to Source Charge	Q _{gs}			nC
V _{GS} = 10 V, I _D = 38.0 A, V _{DS} = 50 V 2N6764T1			22	
V _{GS} = 10 V, I _D = 30.0 A, V _{DS} = 100 V 2N6766T1			22	
V _{GS} = 10 V, I _D = 14.0 A, V _{DS} = 200 V 2N6768T1			18	
V _{GS} = 10 V, I _D = 12.0 A, V _{DS} = 250 V 2N6770T1			19	
Gate to Drain Charge	Q _{gd}			nC
V _{GS} = 10 V, I _D = 38.0 A, V _{DS} = 50 V 2N6764T1			65	
V _{GS} = 10 V, I _D = 30.0 A, V _{DS} = 100 V 2N6766T1			60	
V _{GS} = 10 V, I _D = 14.0 A, V _{DS} = 200 V 2N6768T1			65	
V _{GS} = 10 V, I _D = 12.0 A, V _{DS} = 250 V 2N6770T1			70	

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-on delay time	t _{d(on)}			ns
I _D = 38.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 50 V 2N6764T1				
I _D = 30.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 100 V 2N6766T1			35	
I _D = 14.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 200 V 2N6768T1				
I _D = 12.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 250 V 2N6770T1				
Rise time	t _r			ns
I _D = 38.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 50 V 2N6764T1				
I _D = 30.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 100 V 2N6766T1			190	
I _D = 14.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 200 V 2N6768T1				
I _D = 12.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 250 V 2N6770T1				
Turn-off delay time	t _{d(off)}			ns
I _D = 38.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 50 V 2N6764T1				
I _D = 30.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 100 V 2N6766T1			170	
I _D = 14.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 200 V 2N6768T1				
I _D = 12.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 250 V 2N6770T1				
Fall time	t _f			ns
I _D = 38.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 50 V 2N6764T1				
I _D = 30.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 100 V 2N6766T1			130	
I _D = 14.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 200 V 2N6768T1				
I _D = 12.0 A, V _{GS} = +10 V, R _G = 2.35 Ω, V _{DD} = 250 V 2N6770T1				
Diode Reverse Recovery Time	t _{rr}			ns
di/dt = 100 A/μs, V _{DD} ≤ 30 V, I _D = 38.0 A 2N6764T1			500	
di/dt = 100 A/μs, V _{DD} ≤ 30 V, I _D = 30.0 A 2N6766T1			950	
di/dt = 100 A/μs, V _{DD} ≤ 30 V, I _D = 14.0 A 2N6768T1			1200	
di/dt = 100 A/μs, V _{DD} ≤ 30 V, I _D = 12.0 A 2N6770T1			1600	

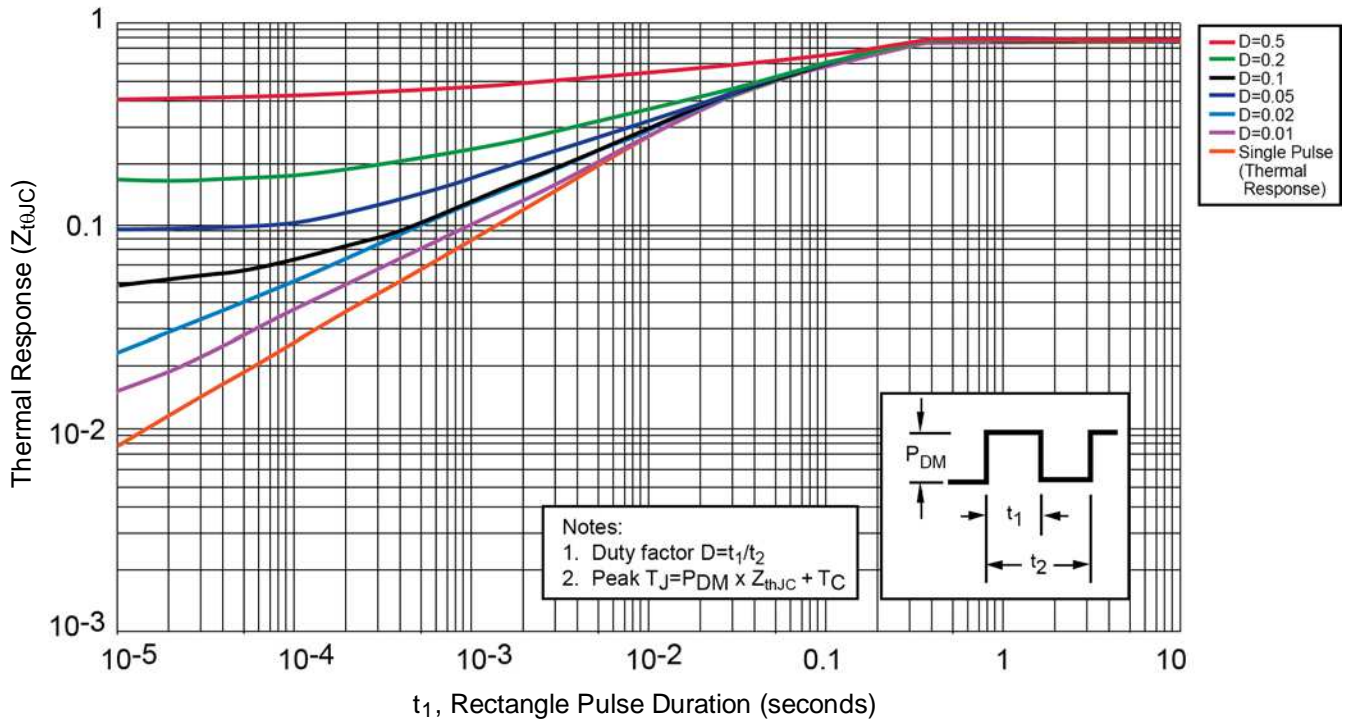
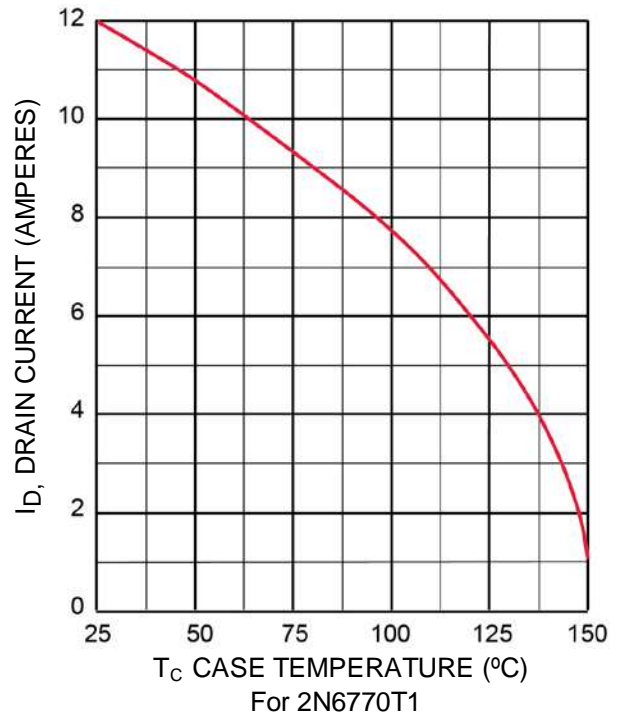
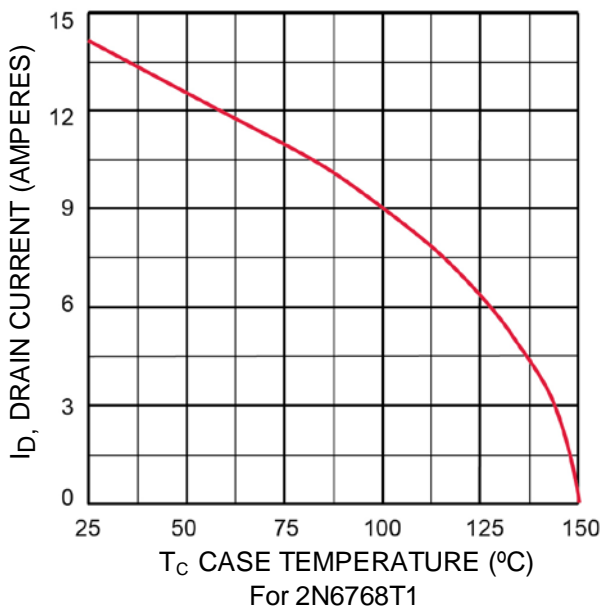
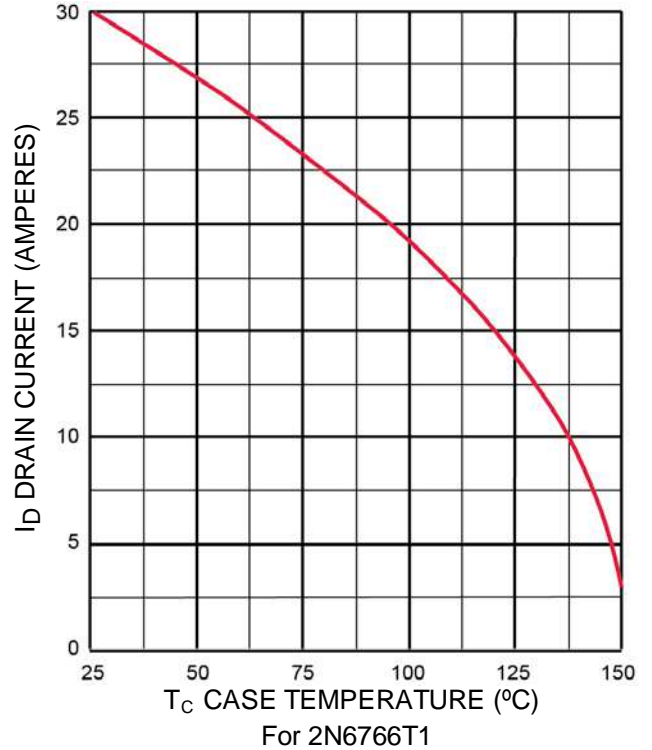
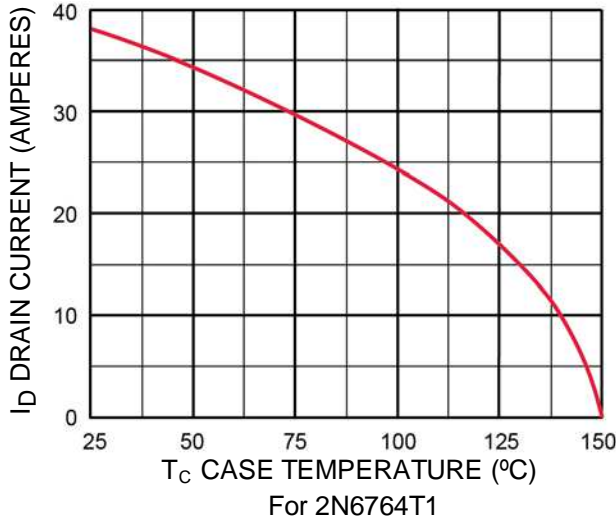
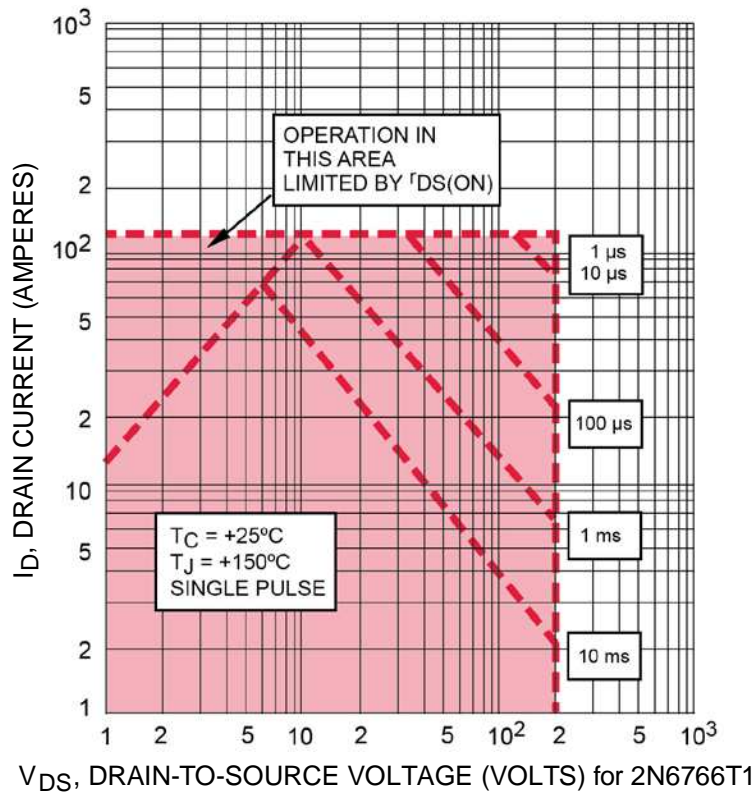
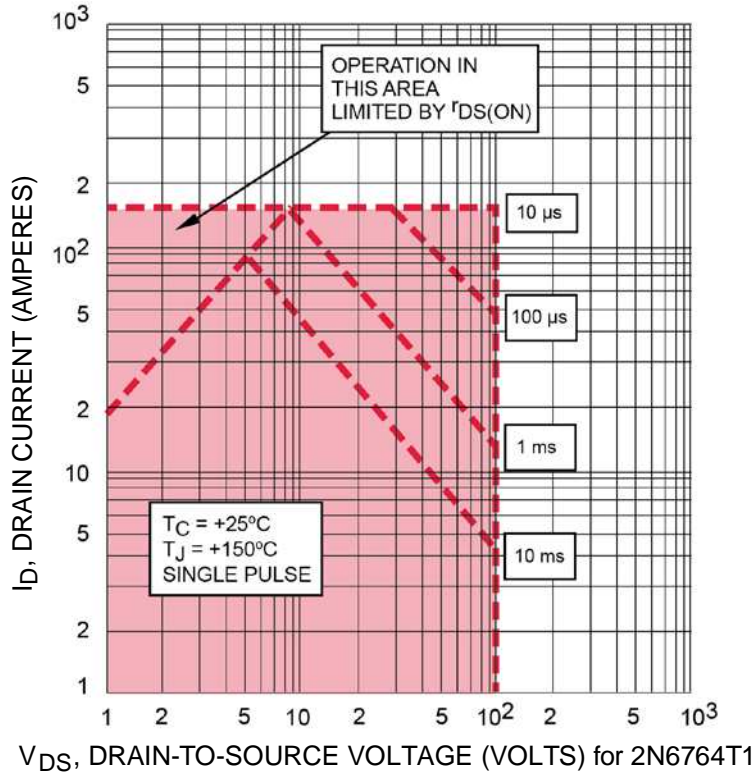
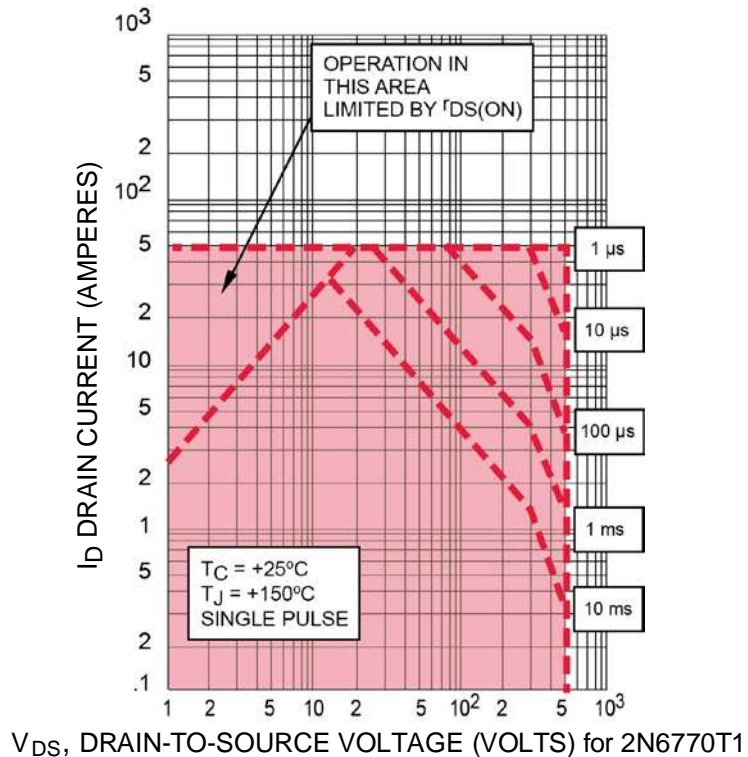
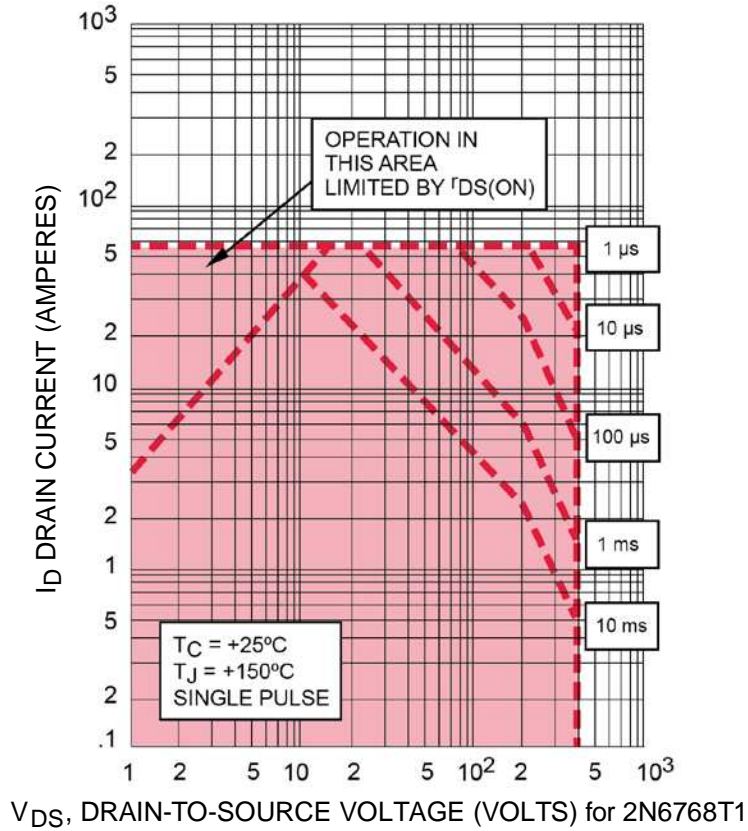
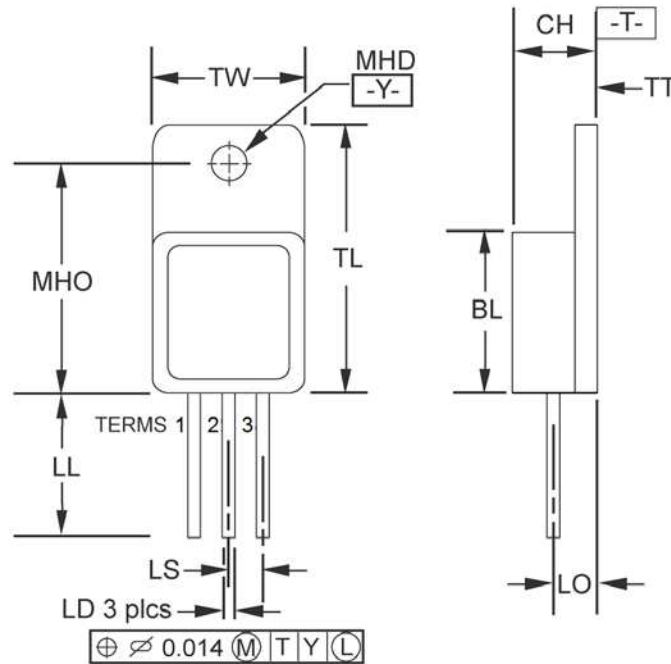
GRAPHS


FIGURE 1
Thermal Response Curves

GRAPHS (continued)
FIGURE 2 – Maximum Drain Current vs Case Temperature Graphs


GRAPHS (continued)
FIGURE 3 – Maximum Safe Operating Area


GRAPHS (continued)


PACKAGE DIMENSIONS

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Protrusion thickness of ceramic eyelets included in dimension LL.
4. All terminals are isolated from case.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

Ltr	Dimensions				Notes
	Inch		Millimeters		
	Min	Max	Min	Max	
BL	0.535	0.545	13.59	13.84	
CH	0.249	0.260	6.32	6.60	
LD	0.035	0.045	0.89	1.14	
LL	0.510	0.570	12.95	14.48	3,4
LO	0.150 BSC		3.81 BSC		
LS	0.150 BSC		3.81 BSC		
MHD	0.139	0.149	3.53	3.78	
MHO	0.665	0.685	16.89	17.40	
TL	0.790	0.800	20.07	20.32	
TT	0.040	0.050	1.02	1.27	
TW	0.535	0.545	13.59	13.84	
Term 1	Drain				
Term 2	Source				
Term 3	Gate				